

5N80G-TA3-T-VB Datasheet

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	800	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	1.2
Q_g (Max.) (nC)	200	
Q_{gs} (nC)	24	
Q_{gd} (nC)	110	
Configuration	Single	

FEATURES

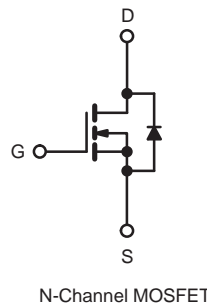
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



TO-220AB



Top View



N-Channel MOSFET



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	800	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25^\circ\text{C}$	A	
		$T_C = 100^\circ\text{C}$		
Pulsed Drain Current ^a	I_{DM}	21		
Linear Derating Factor		1.5	$\text{W}/^\circ\text{C}$	
Single Pulse Avalanche Energy ^b	E_{AS}	770	mJ	
Repetitive Avalanche Current ^a	I_{AR}	7.8	A	
Repetitive Avalanche Energy ^a	E_{AR}	19	mJ	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	190	W
Peak Diode Recovery dV/dt ^c		dV/dt	2.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}		- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$ V, starting $T_J = 25^\circ\text{C}$, $L = 23$ mH, $R_g = 25$ Ω , $I_{AS} = 7.8$ A (see fig. 12).
- $I_{SD} \leq 7.8$ A, $dI/dt \leq 140$ A/ μs , $V_{DD} \leq 600$ V, $T_J \leq 150^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.65	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	800	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.98	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	-	-	100	μA
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}^b$	-	1.2	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 100\text{ V}, I_D = 3.7\text{ A}^b$	5.6	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	3100	-	pF
Output Capacitance	C_{oss}		-	800	-	
Reverse Transfer Capacitance	C_{rss}		-	490	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}, I_D = 3.8\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	200	nC
Gate-Source Charge	Q_{gs}		-	-	24	
Gate-Drain Charge	Q_{gd}		-	-	110	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 3.8\text{ A}, R_g = 6.2\text{ }\Omega, R_D = 52\text{ }\Omega$ see fig. 10 ^b	-	19	-	ns
Rise Time	t_r		-	38	-	
Turn-Off Delay Time	$t_{d(off)}$		-	120	-	
Fall Time	t_f		-	39	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	5.0	-	nH
Internal Source Inductance	L_S		-	13	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.0	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	21	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 3.8\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	650	980	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.8	5.7	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$



Fig. 3 - Typical Transfer Characteristics



Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

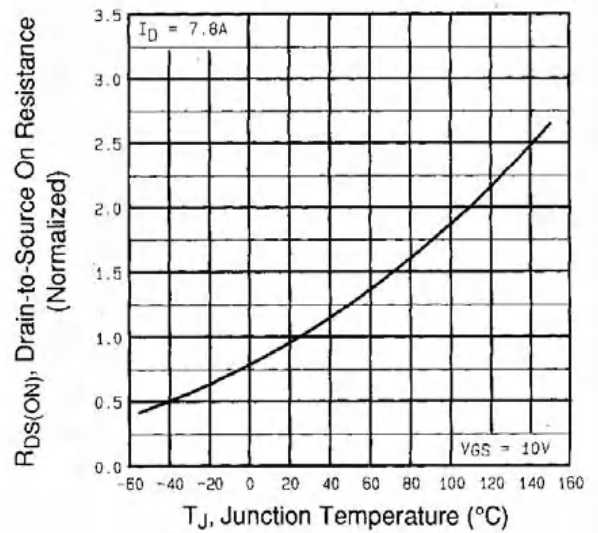


Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

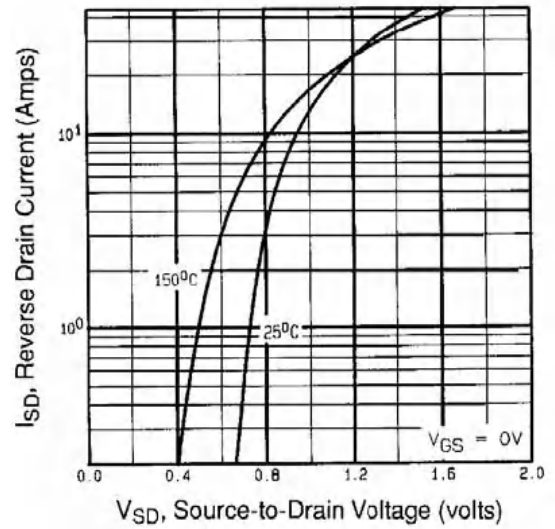


Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

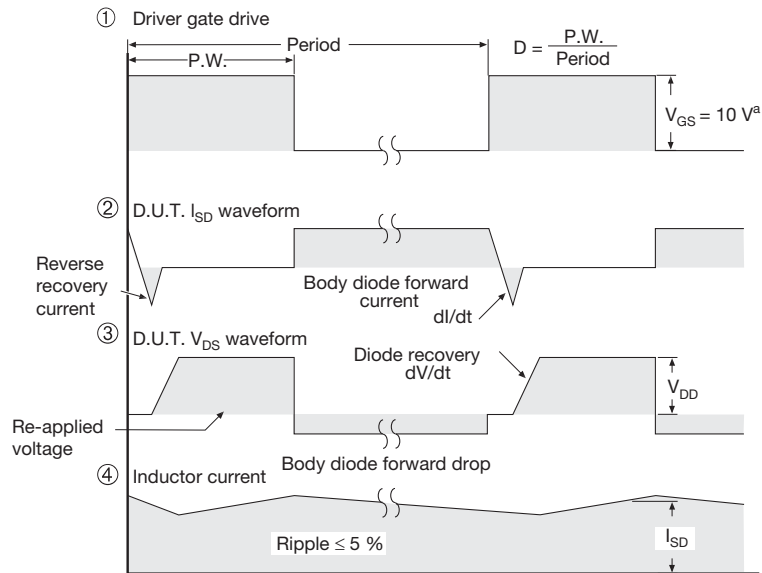
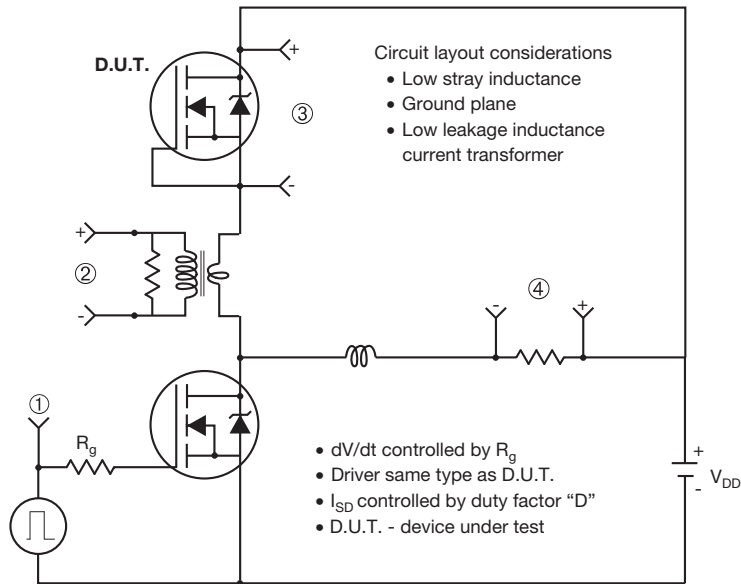


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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